



#### **DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
50V	$1.6\Omega$ @ $V_{GS} = 10V$	350 mA
	$2.5\Omega$ @ $V_{GS}$ = $4.5V$	200 mA

### **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Features and Benefits**

- Dual N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/ Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected to 2KV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (approximate)





Top View



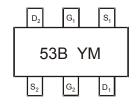
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN53D0LV-7	SOT563	3000/Tape & Reel
DMN53D0LV-13	SOT563	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.dioides.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## Marking Information



53B = Product Type Marking Code (See Note 6) YM = Date Code Marking

Y = Year ex: B = 2014

M = Month ex: 9 = September

Date Code Key

Year	201	4	2015		2016	20	17	2018		2019		2020
Code	В	•	C		D			F		G	-	H
Month	la.	Fal	Man	A	Mari	lone	11	A	0	0-4	Mari	Dan
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

DMN53D0LV
Document number: DS37073 Rev. 2 - 2



### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	$V_{DSS}$	50	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Drain Current (Note 5)	I <sub>D</sub>	350	mA

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

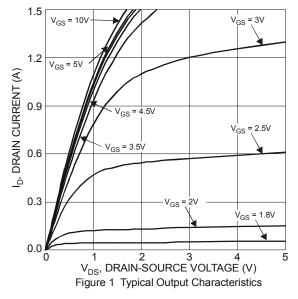
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_{D}$	430	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ hetaJA}$	294	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

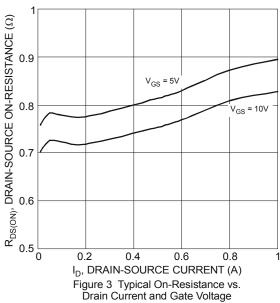
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)	Oymbor		1.36	max	Ome	103t Gondition	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	50	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1.0	μΑ	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V	
Gate-Body Leakage	I <sub>GSS</sub>	_	_	10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.8		1.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
		_	_	1.6		$V_{GS}$ = 10V, $I_{D}$ = 500mA	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	_	_	2.5	Ω	$V_{GS} = 4.5V, I_D = 200mA$	
			_	4.5		$V_{GS} = 2.5V, I_D = 100mA$	
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	0.5	_	1.4	V	$V_{GS} = 0V, I_{S} = 500mA$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C <sub>iss</sub>	_	46	_	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V – f = 1.0MHz	
Output Capacitance	Coss	_	5.3	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	4.0	_	pF	-1 - 1.0IVII IZ	
Total Gate Charge	Qg	_	0.6	_	nC	\	
Gate-Source Charge	$Q_{gs}$	_	0.2	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 250 \text{mA}$	
Gate-Drain Charge	$Q_{gd}$	_	0.1	_	nC	ID = ZOUIIA	
Turn-On Delay Time	t <sub>D(on)</sub>	_	2.7	_	ns		
Turn-On Rise Time	t <sub>r</sub>	_	2.5	_	ns	$V_{DD}$ = 30V, $V_{GS}$ = 10V, $R_{G}$ = 25 $\Omega$ , $I_{D}$ = 200mA	
Turn-Off Delay Time	$t_{D(off)}$		19	_	ns		
Turn-Off Fall Time	t <sub>f</sub>		11	_	ns		

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.6. Short duration pulse test used to minimize self-heating effect.7. Guaranteed by design. Not subject to product testing.







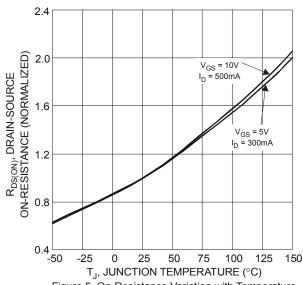
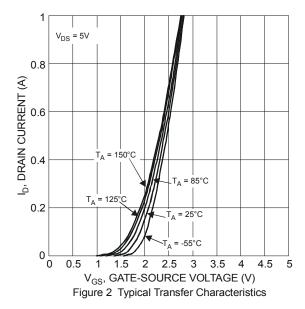
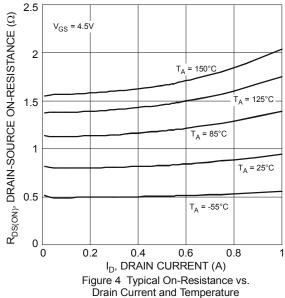


Figure 5 On-Resistance Variation with Temperature





2  $R_{DS(ON)}$ , DRAIN-SOURCE ON-RESISTANCE  $(\Omega)$ 1.8 1.6 1.4  $V_{GS} = 5V$  $I_D = 300 \text{mA}$ 1.2 V<sub>GS</sub> = 10V I<sub>D</sub> = 500mA 8.0 0.6 0 5 0 25 50 75 100 12  ${\sf T_J}$ , JUNCTION TEMPERATURE (°C) -50 -25 125 150

Figure 6 On-Resistance Variation with Temperature



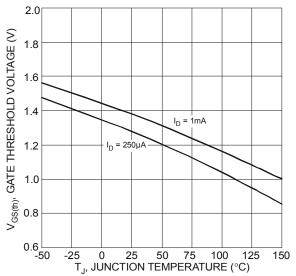
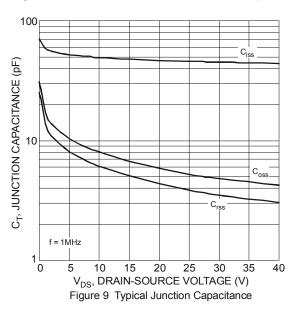
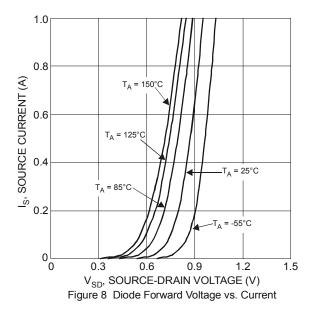
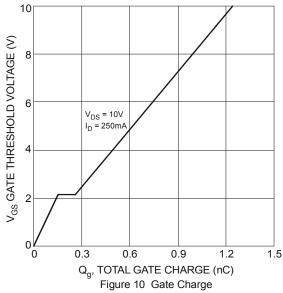


Figure 7 Gate Threshold Variation vs. Ambient Temperature

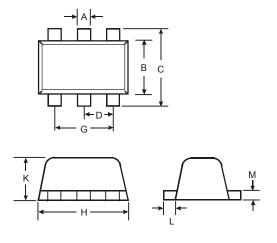






### **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

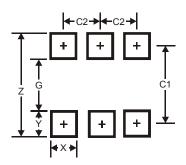


SOT563						
Dim	Min	Max	Тур			
Α	0.15	0.30	0.20			
В	1.10	1.25	1.20			
С	1.55	1.70	1.60			
D	-	-	0.50			
G	0.90	1.10	1.00			
Н	1.50	1.70	1.60			
K	0.55	0.60	0.60			
٦	0.10	0.30	0.20			
М	0.10	0.18	0.11			
All Dimensions in mm						



### Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Υ	0.5
C1	1.7
C2	0.5

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